TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC2782

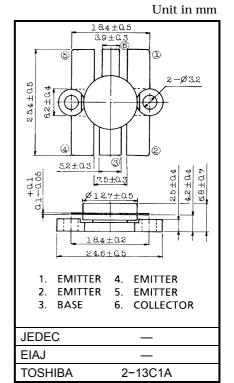
VHF BAND POWER AMPLIFIER APPLICATIONS

• Output Power : Po = 80W (Min.)

 $(f = 175MHz, V_{CC} = 12.5V, Pi = 18W)$

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	36	٧
Collector-Emitter Voltage	V _{CEO}	16	>
Emitter-Base Voltage	V _{EBO}	4	>
Collector Current	Ic	20	Α
Collector Power Dissipation	PC	220	W
Junction Temperature	Tj	175	°C
Storage Temperature Range	T _{stg}	-65~175	°C



Weight: 5.5g

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damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal semigrophy of the computer of the semigrophy of the computer of the semigrophy o

• The information contained herein is subject to change without notice.

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ELECTRICAL CHARACTERISTICS (Tc = 25°C)

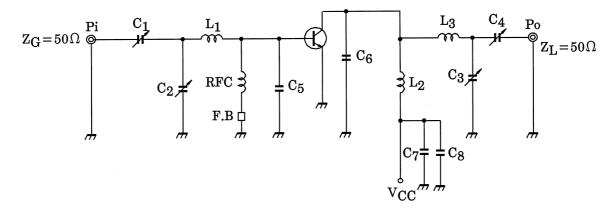
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	V (BR) CBO	I _C = 20mA, I _E = 0	36	_	_	V
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = 50mA, I _B = 0	16	_	_	٧
Emitter-Base Breakdown Voltage	V (BR) EBO	I _E = 1mA, I _C = 0	4	_	_	٧
DC Current Gain	h _{FE}	V _{CE} = 5V, I _C = 10A *	10			
Collector Output Capacitance	C _{ob}	V _{CB} = 12.5V, I _E = 0 f = 1MHz	_	-	320	pF
Output Power	Po	(Fig.) V _{CC} = 12.5V, f = 175MHz	80	90	_	W
Power Gain	Gp		6.4	6.8	_	dB
Collector Efficiency	ηс	Pi = 18W	60	70		%
Series Equivalent Input Impedance	Z _{in}	V _{CC} = 12.5V	_	1.0 +j1.5	_	Ω
Series Equivalent Output Impedance	Z _{out}	f = 175MHz, Po = 80W	_	1.2 +j1.8		Ω

^{*} Pulse Test: Pulse Width ≤ 100µs, Duty Cycle ≤ 3%

CAUTION

Beryllia Ceramics is used in this product. The dust or vapor can be dangerous to humans. Do not break, cut, crush or dissolve chemically. Dispose of this product properly according to law. Do not intermingle with normal industrial or domestic waste.

Fig. Po TEST CIRCUIT



 $C_1 \sim C_4 : \sim 20 pF$

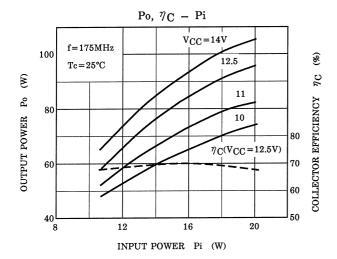
 C_5 : $156 pF (39 pF \times 4)$ CERAMIC CONDENSER C_6 : $132 pF (33 pF \times 4)$ CERAMIC CONDENSER

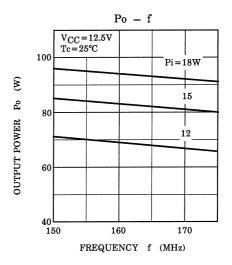
 C_7 : $0.01 \mu F$ CERAMIC CONDENSER

 C_8 : $10\mu F$

L₁, L₃ : ϕ 1.5mm SILVER PLATED COPPER WIRE, 10ID, 1T L₂ : ϕ 1.5mm SILVER PLATED COPPER WIRE, 10ID, 2T RFC : ϕ 1mm ENAMEL COATED COPPER WIRE, 6ID, 10T

FB : FERRITE BEAD





CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.